BL Galaxy Electrical

Silicon Epitaxial Planar Transistor

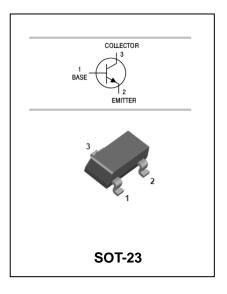
S8050

FEATURES

- High Collector Current.(I_C= 500mA)
- Complementary To S8550.
- Excellent H_{FE} Linearity.
- High total power dissipation.(P_C=300mW)

APPLICATIONS

High Collector Current.



ORDERING INFORMATION

Type No.	Marking	Package Code
S8050	J3Y	SOT-23

MAXIMUM RATING @ Ta=25℃ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	40	V
V _{CEO}	Collector-Emitter Voltage	25	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current -Continuous	500	mA
P _C	Collector Dissipation	300	mW
T_{j},T_{stg}	Junction and Storage Temperature	-55~150	\mathbb{C}

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Rev.A



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ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100μΑ,I _E =0	40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =0.1mA,I _B =0	25			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA,I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =40V,I _E =0			0.1	μA
Collector cut-off current	I _{CEO}	V _{CE} =20V,I _B =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =5V,I _C =0			0.1	μΑ
DC aurent asia		V _{CE} =1V,I _C =50mA	120		350	
DC current gain	h _{FE}	V _{CE} =1V,I _C =500mA	50			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =500mA, I _B = 50mA			0.6	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =500mA, I _B = 50mA			1.2	V
Transition frequency	f⊤	V _{CE} =6V, I _C = 20mA f=30MHz	150			MHz

CLASSIFICATION OF $h_{\text{FE}(1)}$

Rank	L	н
Range	120-200	200-350

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TYPICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

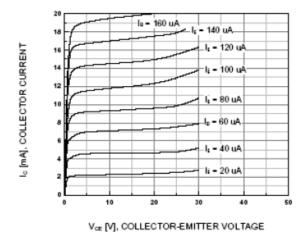


Figure 1. Static Characteristic

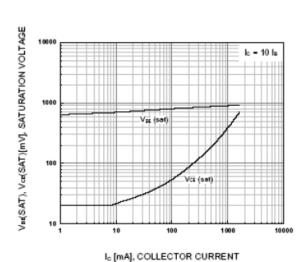


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

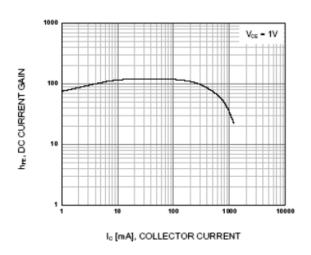


Figure 2. DC current Gain

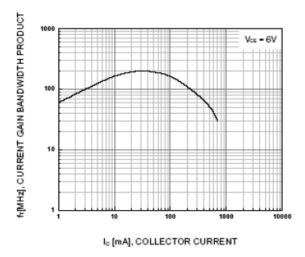


Figure 4. Current Gain Bandwidth Product

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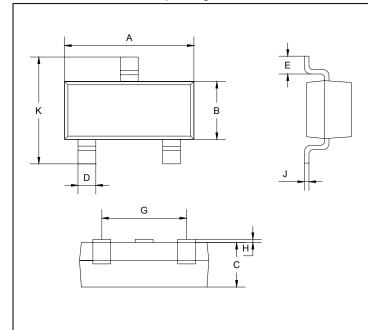
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PACKAGE OUTLINE

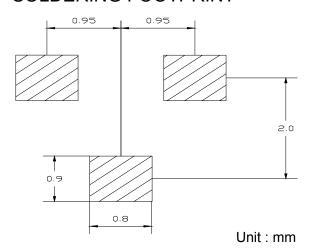
Plastic surface mounted package





SOT-23		
Dim	Min	Max
Α	2.85	2.95
В	1.25	1.35
С	1.0Typical	
D	0.37	0.43
Е	0.35	0.48
G	1.85	1.95
Н	0.02	0.1
J	0.1Typical	
K	2.35	2.45
All Dimensions in mm		

SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
S8050	SOT-23	3000/Tape&Reel